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1	2861539	@ad<19990615	USPAT	2004/09/06 16:58
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4	1686	recombinat\$ and tunnel\$	USPAT	2004/09/06 16:58
5	168	recombinat\$ with tunnel\$	USPAT	2004/09/06 16:59
6	124	@ad<19990615 and (recombinat\$ with tunnel\$)	USPAT	2004/09/06 16:59
7	35865	Poole\$	USPAT	2004/09/06 16:59
8	0	(@ad<19990615 and (recombinat\$ with tunnel\$)) and Poole\$	USPAT	2004/09/06 16:59
9	88	Poole\$ same barrier	USPAT	2004/09/06 17:00
10	102	poole-frenkel	USPAT	2004/09/06 17:00
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13	0	dirac with coulomb\$ with tunnel\$	USPAT	2004/09/06 17:16
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16	2	dirac same coulomb\$	USPAT	2004/09/06 17:15
17	2	@ad<19990615 and (dirac same coulomb\$ )	USPAT	2004/09/06 17:15
18	6	dirac with tunnel\$	USPAT	2004/09/06 17:16
19	15	dirac same tunnel\$	USPAT	2004/09/06 17:16
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25	428	438/158.cccls.	USPAT	2004/09/06 17:34
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27	2066	703/6.cccls. or 703/13.cccls. or 703/14.cccls. or 257/366.cccls. or 438/158.cccls. or 438/172.cccls.	USPAT	2004/09/06 17:34
28	1606	@ad<19990615 and (703/6.cccls. or 703/13.cccls. or 703/14.cccls. or 257/366.cccls. or 438/158.cccls. or 438/172.cccls.)	USPAT	2004/09/06 17:35
29	14	(@ad<19990615 and (703/6.cccls. or 703/13.cccls. or 703/14.cccls. or 257/366.cccls. or 438/158.cccls. or 438/172.cccls.)) and dirac	USPAT	2004/09/06 17:35
30	79	(@ad<19990615 and (703/6.cccls. or 703/13.cccls. or 703/14.cccls. or 257/366.cccls. or 438/158.cccls. or 438/172.cccls.)) and tunnel\$	USPAT	2004/09/06 17:35
31	10	(@ad<19990615 and (703/6.cccls. or 703/13.cccls. or 703/14.cccls. or 257/366.cccls. or 438/158.cccls. or 438/172.cccls.)) and coulomb\$	USPAT	2004/09/06 17:36

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dirac and tunnelling

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**1 Capacitances in double-barrier tunneling structures**

Genoe, J.; Van Hoof, C.; Van Roy, W.; Smet, J.H.; Fobelets, K.; Mertens, R.P.; Borghs, G.;

Electron Devices, IEEE Transactions on, Volume: 38, Issue: 9, Sept. 1991  
Pages:2006 - 2012[\[Abstract\]](#) [\[PDF Full-Text \(548 KB\)\]](#) **IEEE JNL****2 Temperature model for current gain of tunnelling field-induced junction transistors**

Zhen Jiang; Wei Tongli; Feng Yaolan;

Electronics Letters, Volume: 25, Issue: 6, 6 March 1989  
Pages:419 - 420[\[Abstract\]](#) [\[PDF Full-Text \(172 KB\)\]](#) **IEE JNL****3 Fast interface characterization of tunnel oxide MOS structures**

Sell, B.; Schumann, D.; Krautschneider, W.H.;

Nanotechnology, IEEE Transactions on, Volume: 1, Issue: 2, June 2002  
Pages:110 - 113[\[Abstract\]](#) [\[PDF Full-Text \(547 KB\)\]](#) **IEEE JNL****4 Voltage- and temperature-dependent gate capacitance and current model: application to ZrO<sub>2</sub>/n-channel MOS capacitor**

Yang-Yu Fan; Nieh, R.E.; Lee, J.C.; Lucovsky, G.; Brown, G.A.; Register, L.F.; Banerjee, S.K.;

Electron Devices, IEEE Transactions on, Volume: 49, Issue: 11, Nov. 2002  
Pages:1969 - 1978**BEST AVAILABLE COPY**

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[\[Abstract\]](#) [\[PDF Full-Text \(509 KB\)\]](#) [IEEE JNL](#)**5 Numerical simulation of the current-voltage characteristics of heteroepitaxial Schottky-barrier diodes**

Bhapkar, U.V.; Mattauch, R.J.;  
Electron Devices, IEEE Transactions on, Volume: 40, Issue: 6, June 1993  
Pages:1038 - 1046

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